

MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



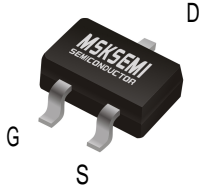
GDT



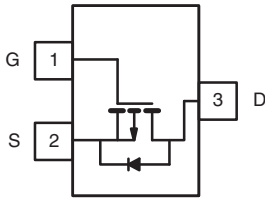
PLED

Product data sheet

www.msksemi.com



SOT-23



Features

- -60V, -1.8A, $R_{DS(ON)} = 200m\Omega @ V_{GS} = -10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Motor Drive
- Power Tools
- LED Lighting

BVDSS	RDSON	ID
-60V	200mΩ	-1.8A

Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A=25^\circ C$)	-1.8	A
	Drain Current – Continuous ($T_A=70^\circ C$)	-1.5	A
I_{DM}	Drain Current – Pulsed ¹	-8	A
P_D	Power Dissipation ($T_A=25^\circ C$)	1.56	W
	Power Dissipation – Derate above 25°C	0.012	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-60	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.05	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-60V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-48V, V _{GS} =0V, T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-1.8A	---	200	300	mΩ
		V _{GS} =-4.5V, I _D =-1.5A	---	300	400	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.7	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	5	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-2A	---	3.5	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2, 3}	V _{DS} =-30V, V _{GS} =-10V, I _D =-2A	---	8.2	---	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	1.8	---	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	1.5	---	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =-30V, V _{GS} =-10V, R _G =6Ω I _D =-1A	---	5.2	---	ns
T _r	Rise Time ^{2, 3}		---	19	---	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	35	---	
T _f	Fall Time ^{2, 3}		---	10.6	---	
C _{iss}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, F=1MHz	---	425	---	pF
C _{oss}	Output Capacitance		---	35	---	
C _{rss}	Reverse Transfer Capacitance		---	20	---	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	---	17	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-1.8	A
I _{SM}	Pulsed Source Current		---	---	-3.6	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

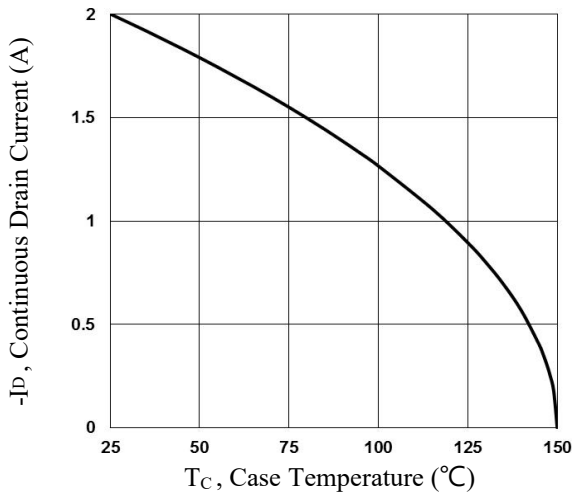


Fig.1 Continuous Drain Current vs. T_c

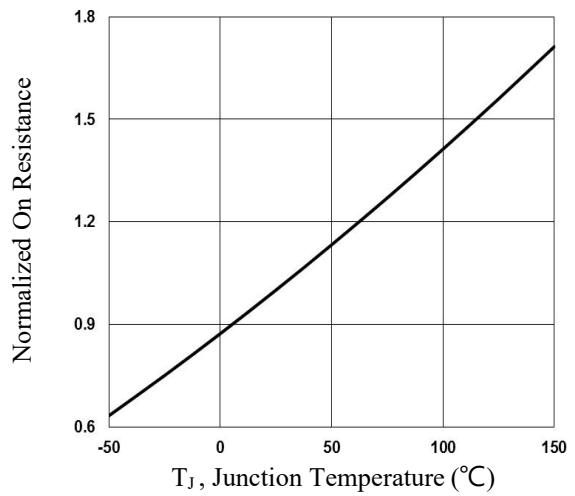


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

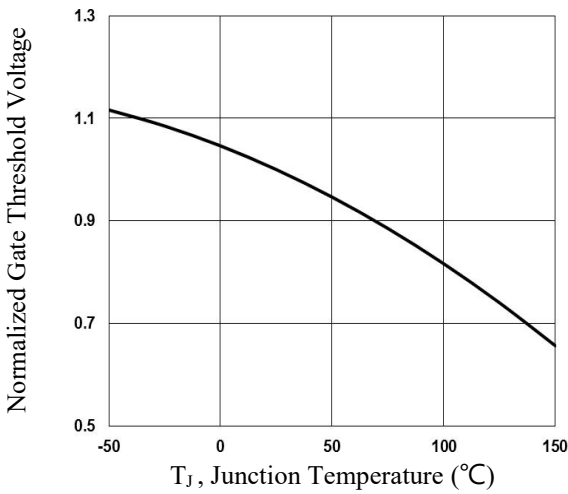


Fig.3 Normalized V_{th} vs. T_j

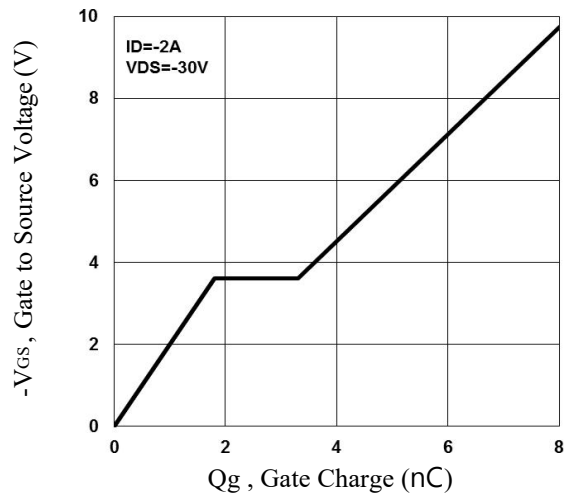


Fig.4 Gate Charge Waveform

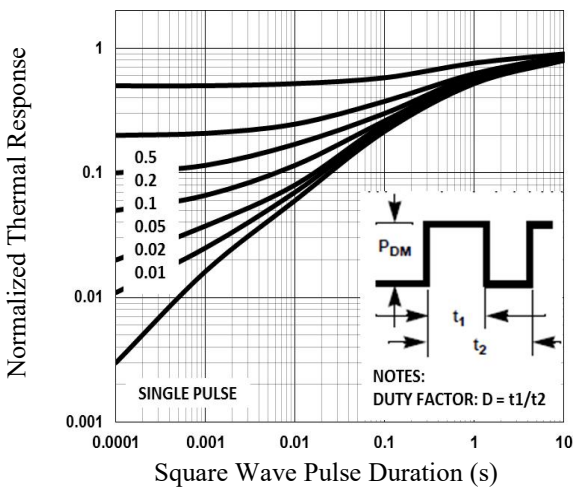


Fig.5 Normalized Transient Impedance

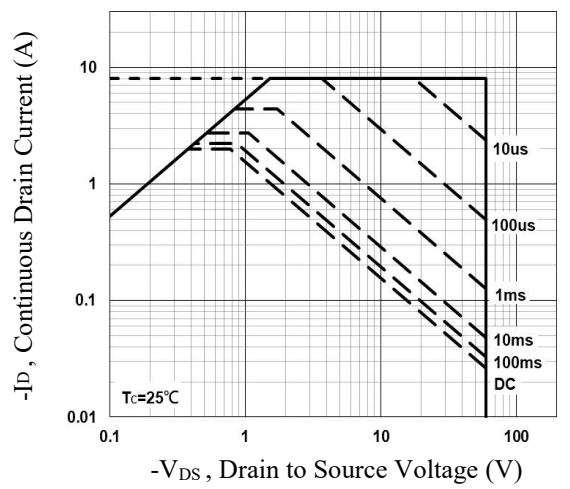
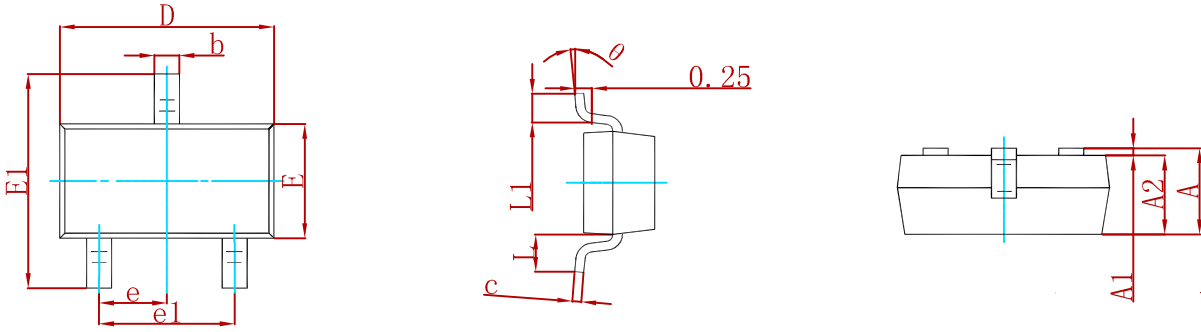


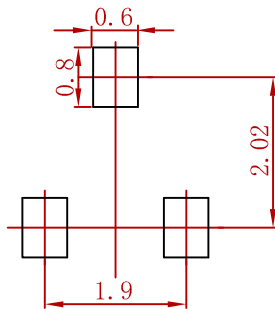
Fig.6 Maximum Safe Operation Area

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SI2309CDS-T1-GE3-MS	SOT-23	3000

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